



Bipolar NPN Bare Die – BTN193

Part Description

The BTN193 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = 60V
- VCEO = 40V
- VEBO = 6V
- hFE = 90-333 @ VCE = 1V, IC = 0.01A
- VCE(Sat) = 0.3V @ IC = 0.05A, IB = 5mA
- fT = 250 MHz @ VCE = 20V, IE = 0A
- COBO = 4pF @ VCB = 5V

Features

Low VCE(sat)

Die Size (Unawn)

320µm X 440µm, 13 Mils X 17 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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